REVISIONS			
LTR	DESCRIPTION	DATE (YR-MO-DA)	APPROVED
A	Add device type 02. Add case outlines L and 3. Add vendor CAGE 01295. Change vendor CAGE 07263 to 27014. Technical and editorial changes throughout.	91-04-22	M. A. Frye
B	Add B, S, Q, and V test limits. Change to one part-one part number format. Add ground bounce and latch-up immunity tests. Add 10.1 substitution statement. Changes to table I. Editorial changes throughout.	92-07-09	Monica L. Poelking
C	Changes made IAW NOR 5962-R161-93.	93-05-21	Monica L. Poelking
D	Make corrections to V_{OL3} limits in table I. Update drawing to MIL-PRF-38535 requirements. - CFS	01-06-29	Thomas M. Hess

REV																				
SHEET																				
REV	D	D	D	D	D	D	D	D	D	D	D	D								
SHEET	15	16	17	18	19	20	21	22	23	24	25	26								

REV STATUS	REV	D	D	D	D	D	D	D	D	D	D	D	D	D
OF SHEETS	SHEET	1	2	3	4	5	6	7	8	9	10	11	12	13	14

PMIC N/A

PREPARED BY
Greg Pitz

DEFENSE SUPPLY CENTER COLUMBUS
COLUMBUS, OHIO 43216
http://www.dscc.dla.mil

STANDARD MICROCIRCUIT DRAWING

THIS DRAWING IS AVAILABLE FOR USE BY ALL DEPARTMENTS

AND AGENCIES OF THE DEPARTMENT OF DEFENSE

AMSC N/A

CHECKED BY
D. A. DiCenzo

APPROVED BY
Michael A. Frye

DRAWING APPROVAL DATE
87-12-23

REVISION LEVEL
D

MICROCIRCUIT, DIGITAL, ADVANCED CMOS, OCTAL BUFFER/LINE DRIVER, WITH THREE-STATE OUTPUTS, TTL COMPATIBLE INPUTS, MONOLITHIC SILICON

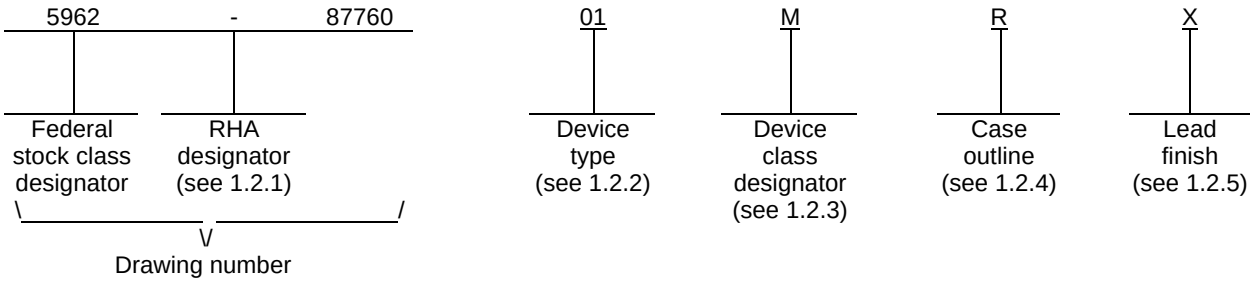
SIZE	CAGE CODE	
A	**67268**	**5962-87760**

SHEET 1 OF 26

1. SCOPE

1.1 Scope. This drawing documents two product assurance class levels consisting of high reliability (device classes M, B and Q) and space application (device classes S and V). A choice of case outlines and lead finishes are available and are reflected in the Part or Identifying Number (PIN). When available, a choice of Radiation Hardness Assurance (RHA) levels are reflected in the PIN.

1.2 PIN. The PIN is as shown in the following example:



1.2.1 RHA designator. Device classes Q and V RHA marked devices meet the MIL-PRF-38535 specified RHA levels and are marked with the appropriate RHA designator. Device class M RHA marked devices meet the MIL-PRF-38535, appendix A specified RHA levels and are marked with the appropriate RHA designator. A dash (-) indicates a non-RHA device.

1.2.2 Device type(s). The device type(s) identify the circuit function as follows:

Device type	Generic number	Circuit function
01	54ACT244	Octal buffer/line driver with non-inverting three-state outputs, TTL compatible inputs
02	54ACT11244	Octal buffer/line driver with non-inverting three-state outputs, TTL compatible inputs

1.2.3 Device class designator. The device class designator is a single letter identifying the product assurance level as follows:

Device class	Device requirements documentation
M	Vendor self-certification to the requirements for MIL-STD-883 compliant, non-JAN class level B microcircuits in accordance with MIL-PRF-38535, appendix A
B or S	Certification and qualification to MIL-PRF-38535, appendix A
Q or V	Certification and qualification to MIL-PRF-38535

1.2.4 Case outline(s). The case outline(s) are as designated in MIL-STD-1835 and as follows:

Outline letter	Descriptive designator	Terminals	Package style
R	GDIP1-T20 or CDIP2-T20	20	Dual-in-line
S	GDFP2-F20 or CDFP3-F20	20	Flat pack
L	GDIP3-T24 or CDIP4-T24	24	Dual-in-line
2	CQCC1-N20	20	Square leadless chip carrier
3	CQCC1-N28	28	Square leadless chip carrier

1.2.5 Lead finish. The lead finish is as specified in MIL-PRF-38535 for device classes Q and V or MIL-PRF-38535, appendix A for device class M, B and S.

1.3 Absolute maximum ratings. 1/ 2/

Supply voltage range (V_{CC})	-0.5 V dc to +6.0 V dc
DC input voltage (V_{IN})	-0.5 V dc to V_{CC} +0.5 V dc
DC output voltage range (V_{OUT})	-0.5 V dc to V_{CC} + 0.5 V dc
Clamp diode current (I_{IK}, I_{OK})	±20 mA
DC output current (I_{OUT})	±50 mA
DC V_{CC} or GND current (I_{CC}, I_{GND})	±200 mA 3/
Storage temperature range (T_{STG})	-65°C to +150°C
Maximum power dissipation (P_D)	500 mW
Lead temperature (soldering, 10 seconds)	+300°C
Thermal resistance, junction-to-case (θ_{JC})	See MIL-STD-1835
Junction temperature (T_J)	+175°C
Case operating temperature (T_C)	-55°C to +125°C

1.4 Recommended operating conditions. 1/ 2/ 4/

Supply voltage range (V_{CC})	+4.5 V dc to +5.5 V dc
Input voltage range (V_{IN})	+0.0 V dc to V_{CC}
Output voltage range (V_{OUT})	+0.0 V dc to V_{CC}
Maximum low level input voltage (V_{IL})	0.8 V at V_{CC} = 4.5 V 0.8 V at V_{CC} = 5.5 V
Minimum high level input voltage (V_{IH})	2.0 V at V_{CC} = 4.5 V 2.0 V at V_{CC} = 5.5 V
Case operating temperature range (T_C)	-55°C to +125°C
Input rise and fall rate (t_r, and t_f) maximum:	
V_{CC} = 4.5 V	10 ns/V
V_{CC} = 5.5 V	8 ns/V
Maximum high level output current (I_{OH})	-24 mA
Maximum low level output current (I_{OL})	24 mA

1/ Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability. The maximum junction temperature may be exceeded for allowable short duration burn-in screening conditions in accordance with method 5004 of MIL-STD-883.

2/ Unless otherwise noted, all voltages are referenced to GND.

3/ For packages with multiple V_{CC} and GND pins, this value represents the maximum total current flowing into or out of all V_{CC} or GND pins.

4/ Unless otherwise specified, the values listed above shall apply over the full V_{CC} and T_C recommended operating range.

2. APPLICABLE DOCUMENTS

2.1 Government specification, standards, and handbooks. The following specification, standards, and handbooks form a part of this drawing to the extent specified herein. Unless otherwise specified, the issues of these documents are those listed in the issue of the Department of Defense Index of Specifications and Standards (DoDISS) and supplement thereto, cited in the solicitation.

SPECIFICATION

DEPARTMENT OF DEFENSE

MIL-PRF-38535 - Integrated Circuits, Manufacturing, General Specification for.

STANDARDS

DEPARTMENT OF DEFENSE

MIL-STD-883 - Test Method Standard Microcircuits.
MIL-STD-1835 - Interface Standard Electronic Component Case Outlines.

HANDBOOKS

DEPARTMENT OF DEFENSE

MIL-HDBK-103 - List of Standard Microcircuit Drawings.
MIL-HDBK-780 - Standard Microcircuit Drawings.

(Unless otherwise indicated, copies of the specification, standards, and handbooks are available from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

2.2 Non-Government publications. The following document(s) form a part of this document to the extent specified herein. Unless otherwise specified, the issues of the documents which are DoD adopted are those listed in the issue of the DoDISS cited in the solicitation. Unless otherwise specified, the issues of documents not listed in the DoDISS are the issues of the documents cited in the solicitation.

ELECTRONIC INDUSTRIES ALLIANCE (EIA)

JEDEC Standard No. 17 - A Standardized Test Procedure for the Characterization of the LATCH-UP in CMOS Integrated Circuits

JEDEC Standard No. 20 - Standardized for Description of 54/74ACXXXX and 54/74ACTXXXX Advanced High-Speed CMOS Devices

(Applications for copies should be addressed to the Electronics Industries Alliance, 2001 Eye Street, NW, Washington DC 20006.)

(Non-Government standards and other publications are normally available from the organizations that prepare or distribute the documents. These documents may also be available in or through libraries or other informational services.)

2.3 Order of precedence. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

3.1 Item requirements. The individual item requirements for device classes Q and V shall be in accordance with MIL-PRF-38535 and as specified herein or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. The individual item requirements for device class M shall be in accordance with MIL-PRF-38535, appendix A for non-JAN class level B devices and as specified herein. The individual item requirements for device classes B and S shall be in accordance with MIL-PRF-38535, appendix A and as specified herein. This is a fully characterized military detail specification and is suitable for qualification of device classes B and S to the requirements of MIL-PRF-38535, appendix A.

3.2 Design, construction, and physical dimensions. The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535 and herein for device classes Q and V or MIL-PRF-38535, appendix A and herein for device classes M, B and S.

3.2.1 Case outlines. The case outlines shall be in accordance with 1.2.4 herein.

3.2.2 Terminal connections. The terminal connections shall be as specified on figure 1.

3.2.3 Truth table. The truth table shall be as specified on figure 2.

3.2.4 Logic diagram. The logic diagram shall be as specified on figure 3.

3.2.5 Ground bounce load circuit and waveforms. The ground bounce load circuit and waveforms shall be as specified on figure 4.

3.2.6 Switching waveforms and test circuit. The switching waveforms and test circuit shall be as specified on figure 5.

3.2.7 Radiation exposure circuit. The radiation exposure circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing and acquiring activity upon request.

3.2.8 Schematic Circuits. The schematic circuits shall be submitted to the preparing activity prior to the inclusion of a manufacturer's device in this drawing and shall be submitted to the qualifying activity as a prerequisite for qualification for device classes B and S. All qualified manufacturer's schematics shall be maintained and available upon request.

3.3 Electrical performance characteristics and postirradiation parameter limits. Unless otherwise specified herein, the electrical performance characteristics and postirradiation parameter limits are as specified in table I and shall apply over the full case operating temperature range. Test conditions for these specified characteristics and limits are as specified in table I. For device classes B and S, a pin-for-pin conditions and testing sequence for table I parameters shall be maintained and available upon request from the qualifying activity, on qualified devices.

3.4 Electrical test requirements. The electrical test requirements shall be the subgroups specified in table IIA. The electrical tests for each subgroup are defined in table I. Radiation hardness assurance level designators M, D, and R (see MIL-PRF-38535) in table I are post-irradiation end-point electrical parameters.

3.5 Marking. The part shall be marked with the PIN listed in 1.2 herein. In addition, the manufacturer's PIN may also be marked as listed in MIL-HDBK-103. For packages where marking of the entire SMD PIN number is not feasible due to space limitations, the manufacturer has the option of not marking the "5962-" on the device. For RHA product using this option, the RHA designator shall still be marked. Marking for device classes Q and V shall be in accordance with MIL-PRF-38535. Marking for device classes M, B, and S shall be in accordance with MIL-PRF-38535, appendix A.

3.5.1 Certification/compliance mark. The certification mark for device classes Q and V shall be a "QML" or "Q" as required in MIL-PRF-38535. The compliance mark for device class M shall be a "C" as required in MIL-PRF-38535, appendix A. The compliance mark for device classes B and S shall be a "QML" or "Q" as required in MIL-PRF-38535, appendix A.

3.5.2 Correctness of indexing and marking for device classes B and S. For device classes B and S, all devices shall be subjected to the final electrical tests specified in table II after PIN marking (marked in accordance with MIL-PRF-38535, appendix A) to verify that they are correctly indexed and identified by PIN. Optionally, an approved electrical test may be deviced especially for this requirement.

3.6 Certificate of compliance. For device classes B, S, Q and V, a certificate of compliance shall be required from a QML-38535 listed manufacturer in order to supply to the requirements of this drawing (see 6.6.1 herein). For device class M, a certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in MIL-HDBK-103 (see 6.6.2 herein). The certificate of compliance submitted to DSCC-VA prior to listing as an approved source of supply for this drawing shall affirm that the manufacturer's product meets, for device classes Q and V, the requirements of MIL-PRF-38535 and herein or for device classes M, B and S the requirements of MIL-PRF-38535, appendix A and herein.

3.7 Certificate of conformance. A certificate of conformance as required for device classes Q and V in MIL-PRF-38535 or for device classes M, B and S in MIL-PRF-38535, appendix A shall be provided with each lot of microcircuits delivered to this drawing.

3.8 Notification of change for device class M. For device class M, notification to DSCC-VA of change of product (see 6.2 herein) involving devices acquired to this drawing is required for any change as defined in MIL-PRF-38535, appendix A.

3.9 Verification and review for device class M. For device class M, DSCC, DSCC's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.

3.10 Microcircuit group assignment for device classes M, B and S. Device classes M, B and S devices covered by this drawing shall be in microcircuit group number 37 (see MIL-PRF-38535, appendix A).

3.11 Serialization for device class S. All device class S devices shall be serialized in accordance with MIL-PRF-38535, appendix A.

3.12 Substitution. Substitution data shall be as indicated in the appendix herein.

TABLE I. Electrical performance characteristics.

Test and MIL-STD-883 test method 1/	Symbol	Test Conditions 2/ $-55°C \le T_C \le +125°C$ $+4.5\ V \le V_{CC} \le +5.5\ V$ unless otherwise specified		Device type 3/ and device class	V_{CC}	Group A subgroups	Limits 2/		Unit
							Min	Max	
High level output voltage 3006	V_{OH1} 4/	For all inputs affecting output under test $V_{IN} = V_{IH}$ or V_{IL} $V_{IH} = 2.0\ V$ $V_{IL} = 0.8\ V$ For all other inputs, $V_{IN} = V_{CC}$ or GND $I_{OH} = -50\ \mu A$		All All	4.5 V	1, 2, 3	4.4		V
	V_{OH2} 5/ 6/	For all inputs affecting output under test $V_{IN} = V_{IH}$ or V_{IL} $V_{IH} = 2.0\ V$ $V_{IL} = 0.8\ V$		All All	5.5 V	1, 2, 3	5.4		
		For all other inputs, $V_{IN} = V_{CC}$ or GND $I_{OH} = -50\ \mu A$	M	01 B, S, Q, V		1	5.4		
			D				5.4		
			P, L, R				5.4		
	V_{OH3} 5/ 6/	For all inputs affecting output under test $V_{IN} = V_{IH}$ or V_{IL} $V_{IH} = 2.0\ V$ $V_{IL} = 0.8\ V$		All All	4.5 V	1, 2, 3	3.7		
		For all other inputs, $V_{IN} = V_{CC}$ or GND $I_{OH} = -24\ mA$	M	01 B, S, Q, V		1	3.7		
			D				3.7		
			P, L, R				3.7		
	V_{OH4} 4/	For all inputs affecting output under test $V_{IN} = V_{IH}$ or V_{IL} $V_{IH} = 2.0\ V$ $V_{IL} = 0.8\ V$ For all other inputs, $V_{IN} = V_{CC}$ or GND $I_{OH} = -24\ mA$		All All	5.5 V	1, 2, 3	4.7		
	V_{OH5} 5/ 6/ 7/	For all inputs affecting output under test $V_{IN} = V_{IH}$ or V_{IL} $V_{IH} = 2.0\ V$ $V_{IL} = 0.8\ V$		All All	5.5 V	1, 2, 3	3.85		
		For all other inputs, $V_{IN} = V_{CC}$ or GND $I_{OH} = -50\ mA$	M	01 B, S, Q, V		1	3.85		
			D				3.85		
			P, L, R				3.85		

See footnotes at end of table.

TABLE I. Electrical performance characteristics - Continued.

Test and MIL-STD-883 test method 1/	Symbol	Test Conditions 2/ $-55°C \le T_C \le +125°C$ $+4.5\ V \le V_{CC} \le +5.5\ V$ unless otherwise specified		Device type 3/ and device class	V_{CC}	Group A subgroups	Limits 2/		Unit
							Min	Max	
Low level output voltage 3007	V_{OL1} 4/	For all inputs affecting output under test $V_{IN} = V_{IH}$ or V_{IL} $V_{IH} = 2.0\ V$ $V_{IL} = 0.8\ V$ For all other inputs, $V_{IN} = V_{CC}$ or GND $I_{OL} = 50\ \mu A$		All All	4.5 V	1, 2, 3		0.1	V
	V_{OL2} 5/ 6/	For all inputs affecting output under test $V_{IN} = V_{IH}$ or V_{IL} $V_{IH} = 2.0\ V$ $V_{IL} = 0.8\ V$ For all other inputs, $V_{IN} = V_{CC}$ or GND $I_{OL} = 50\ \mu A$		All All	5.5 V	1, 2, 3		0.1	
			M	01		1		0.1	
			D	B, S, Q, V				0.1	
			P, L, R					0.1	
	V_{OL3} 5/ 6/	For all inputs affecting output under test $V_{IN} = V_{IH}$ or V_{IL} $V_{IH} = 2.0\ V$ $V_{IL} = 0.8\ V$		All B, S, Q, V	4.5 V	1, 3		0.4	
						2		0.5	
				All M		1		0.4	
						2, 3		0.5	
		For all other inputs, $V_{IN} = V_{CC}$ or GND $I_{OL} = 24\ mA$	M	01 B, S, Q, V		1		0.4	
			D					0.4	
			P, L, R					0.4	
	V_{OL4} 4/	For all inputs affecting output under test $V_{IN} = V_{IH}$ or V_{IL} $V_{IH} = 2.0\ V$ $V_{IL} = 0.8\ V$		All B, S, Q, V	5.5 V	1, 3		0.4	
						2		0.5	
		For all other inputs, $V_{IN} = V_{CC}$ or GND $I_{OL} = 24\ mA$		All M		1		0.4	
						2,3		0.5	
	V_{OL5} 5/ 6/ 7/	For all inputs affecting output under test $V_{IN} = V_{IH}$ or V_{IL} $V_{IH} = 2.0\ V$ $V_{IL} = 0.8\ V$		All All	5.5 V	1, 2, 3		1.65	
		For all other inputs, $V_{IN} = V_{CC}$ or GND $I_{OL} = 50\ mA$	M	01 B, S, Q, V		1		1.65	
			D					1.65	
			P, L, R					1.65	

See footnotes at end of table.

TABLE I. Electrical performance characteristics - Continued.

Test and MIL-STD-883 test method 1/	Symbol	Test Conditions 2/ $-55°C \le T_C \le +125°C$ $+4.5\ V \le V_{CC} \le +5.5\ V$ unless otherwise specified		Device type 3/ and device class	V_{CC}	Group A subgroups	Limits 2/		Unit
							Min	Max	
Three-state output leakage current high 3021	I_{OZH} 5/ 6/	___ OEn = V_{IH} or V_{IL} V_{IH} = 2.0 V V_{IL} = 0.8 V For all other inputs, V_{IN} = V_{CC} or GND V_{OUT} = 5.5 V		All	5.5 V	1		0.5	µA
				B, S, Q, V		2		10.0	
				All		1		0.5	
				M		2, 3		10.0	
			M	01		1		3.0	
			D	B, S, Q, V				10.0	
			P, L, R					20.0	
Three-state output leakage current low 3020	I_{OZL} 5/ 6/	___ OEn = V_{IH} or V_{IL} V_{IH} = 2.0 V V_{IL} = 0.8 V For all other inputs, V_{IN} = V_{CC} or GND V_{OUT} = GND		All	5.5 V	1		-0.5	µA
				B, S, Q, V		2		-10.0	
				All		1		-0.5	
				M		2, 3		-10.0	
			M	01		1		-3.0	
			D	B, S, Q, V				-10.0	
			P, L, R					-20.0	
Positive input clamp voltage 3022	V_{IC+} 5/ 6/	V_{CC} = Open For input under test, I_{IN} = 1 mA		All B, S, Q, V		1	0.4	1.5	V
			M	01		1	0.4	1.5	
			D	B, S, Q, V			0.4	1.5	
			P, L, R				0.4	1.5	
Negative input clamp voltage 3022	V_{IC-} 5/ 6/	V_{CC} = Open For input under test, I_{IN} = -1 mA		All B, S, Q, V		1	-0.4	-1.5	V
			M	01		1	-0.4	-1.5	
			D	B, S, Q, V			-0.4	-1.5	
			P, L, R				-0.4	-1.5	
Input current high 3010	I_{IH} 5/ 6/	For input under test, V_{IN} = V_{CC} For all other inputs, V_{IN} = V_{CC} or GND		All	5.5 V	1		0.1	µA
				B, S, Q, V		2		1.0	
				All		1		0.1	
				M		2, 3		1.0	
			M	01		1		0.1	
			D	B, S, Q, V				0.1	
			P, L, R					0.1	

See footnotes at end of table.

TABLE I. Electrical performance characteristics - Continued.

Test and MIL-STD-883 test method 1/	Symbol	Test Conditions 2/ $-55°C \le T_C \le +125°C$ $+4.5\ V \le V_{CC} \le +5.5\ V$ unless otherwise specified		Device type 3/ and device class	V_{CC}	Group A subgroups	Limits 2/		Unit
							Min	Max	
Input current low 3009	I_{IL} 5/ 6/	For input under test, V_{IN} = GND For all other inputs, $V_{IN} = V_{CC}$ or GND		All	5.5 V	1		-0.1	µA
				B, S, Q, V		2		-1.0	
				All		1		-0.1	
				M		2, 3		-1.0	
			M	01		1		-0.1	
			D	B, S, Q, V				-0.1	
			P, L, R					-0.1	
Control input capacitance 3012	C_{IN}	See 4.4.1b T_C = +25°C		All	GND	4		10.0	pF
				All					
Output capacitance 3012	C_{OUT}	See 4.4.1b T_C = +25°C		01	5.5 V	4		15.0	pF
				All					
				02	5.0 V	4		20.0	
				All					
Power dissipation capacitance	C_{PD} 9/	See 4.4.1b T_C = +25°C		All	5.0 V	4		65.0	pF
				All					
Quiescent supply current delta, TTL input levels 3005	ΔI_{CC} 5/ 6/ 10/	For input under test, $V_{IN} = V_{CC}$ - 2.1 V For all other inputs, $V_{IN} = V_{CC}$ or GND		All	5.5 V	3		1.6	mA
				B, S, Q, V		1, 2		1.0	
				All		1, 2, 3		1.6	
				M					
			M	01		1		1.6	
			D	B, S, Q, V				1.6	
			P, L, R					3.0	
Quiescent supply current output high 3005	I_{CCH} 5/ 6/	$\overline{OE}n$ = GND For all other inputs, $V_{IN} = V_{CC}$		All	5.5 V	1		2.0	µA
				B, S, Q, V		2		40.0	
				All		1		8.0	
				M		2, 3		160.0	
			M	01		1		300.0	
			D	B, S, Q, V				1.0	
			P, L, R					2.0	
Quiescent supply current output low 3005	I_{CCL} 5/ 6/	$\overline{OE}n$ = GND For all other inputs, V_{IN} = GND		All	5.5 V	1		2.0	µA
				B, S, Q, V		2		40.0	
				All		1		8.0	
				M		2, 3		160.0	
			M	01		1		300.0	
			D	B, S, Q, V				1.0	mA
			P, L, R					2.0	

See footnotes at end of table.

TABLE I. Electrical performance characteristics - Continued.

Test and MIL-STD-883 test method 1/	Symbol	Test Conditions 2/ $-55°C \le T_C \le +125°C$ $+4.5\ V \le V_{CC} \le +5.5\ V$ unless otherwise specified		Device type 3/ and device class	V_{CC}	Group A subgroups	Limits 2/		Unit
							Min	Max	
Quiescent supply current outputs three-state 3005	I_{CCZ} 5/ 6/	$\overline{OEn} = V_{CC}$ For all other inputs, $V_{IN} = V_{CC}$ or GND		All	5.5 V	1		2.0	µA
				B, S, Q, V		2		40.0	
				All		1		8.0	
				M		2, 3		160.0	
			M	01		1		300.0	
			D	B, S, Q, V				1.0	mA
			P, L, R					2.0	
Low level ground bounce noise	V_{GBL} 11/ 12/	$V_{LD} = 2.5\ V$, $I_{OL} = +24\ mA$ (see figure 4)		All B, S, Q, V	4.5 V	4		2000	mV
High level ground bounce noise	V_{GBH} 11/ 12/	$V_{LD} = 2.5\ V$, $I_{OH} = -24\ mA$ (see figure 4)		All B, S, Q, V	4.5 V	4		2000	mV
Latch-up input/ output over-voltage	I_{CC} (O/V1) 13/	$t_w \ge 100\ \mu s$ $t_{cool} \ge t_w$ $5\ \mu s \le t_r \le 5\ ms$ $5\ \mu s \le t_f \le 5\ ms$ $V_{test} = 6.0\ V$ $V_{CCQ} = 5.5\ V$ $V_{over} = 10.5\ V$		All B, S, Q, V	5.5 V	2		200	mA
Latch-up input/ output positive over-current	I_{CC} (O/I1+) 13/	$t_w \ge 100\ \mu s$ $t_{cool} \ge t_w$ $5\ \mu s \le t_r \le 5\ ms$ $5\ \mu s \le t_f \le 5\ ms$ $V_{test} = 6.0\ V$ $V_{CCQ} = 5.5\ V$ $I_{trigger} = +120\ mA$		All B, S, Q, V	5.5 V	2		200	mA
Latch-up input/ output negative over-current	I_{CC} (O/I1-) 13/	$t_w \ge 100\ \mu s$ $t_{cool} \ge t_w$ $5\ \mu s \le t_r \le 5\ ms$ $5\ \mu s \le t_f \le 5\ ms$ $V_{test} = 6.0\ V$ $V_{CCQ} = 5.5\ V$ $I_{trigger} = -120\ mA$		All B, S, Q, V	5.5 V	2		200	mA
Latch-up supply over-voltage	I_{CC} (O/V2) 13/	$t_w \ge 100\ \mu s$ $t_{cool} \ge t_w$ $5\ \mu s \le t_r \le 5\ ms$ $5\ \mu s \le t_f \le 5\ ms$ $V_{test} = 6.0\ V$ $V_{CCQ} = 5.5\ V$ $V_{over} = 9.0\ V$		All B, S, Q, V	5.5 V	2		100	mA

See footnotes at end of table.

TABLE I. Electrical performance characteristics - Continued.

Test and MIL-STD-883 test method 1/	Symbol	Test Conditions 2/ $-55°C \le T_C \le +125°C$ $+4.5\ V \le V_{CC} \le +5.5\ V$ unless otherwise specified		Device type 3/ and device class	V_{CC}	Group A subgroups	Limits 2/		Unit
							Min	Max	
Truth table test output voltage 3014	5/ 6/ 14/	V_{IL} = 0.40 V, V_{IH} = 2.40 V, Verify output V_{OUT} See 4.4.1c		All All	4.5 V	7, 8	L	H	
				All M	5.5 V	7, 8	L	H	
			M	All	4.5 V	7	L	H	
			D	B, S, Q, V			L	H	
			P, L, R				L	H	
Propagation delay time, data to output, mAn to mYn 3003	t_{PHL}, t_{PLH} 5/ 6/ 15/ 16/	C_L = 50 pF minimum, R_L = 500Ω, See figure 5		01 B, S, Q, V	4.5 V	9, 11 10	1.0 1.0	9.0 10.0	ns
				02 B, S, Q, V		9, 11 10	1.0 1.0	8.9 10.6	
				01 M		9 10, 11	1.0 1.0	9.0 10.0	
				02 M		9 10, 11	1.0 1.0	8.9 10.6	
			M	01		9	1.0	9.0	
			D	B, S, Q, V			1.0	9.0	
			P, L, R				1.0	9.0	
Propagation delay time, output enable, OEn to mYn 3003	t_{PZH}, t_{PZL} 5/ 6/ 15/ 16/	C_L = 50 pF minimum, R_L = 500Ω, See figure 5		01 B, S, Q, V	4.5 V	9, 11 10	1.0 1.0	9.0 11.0	ns
				02 B, S, Q, V		9, 11 10	1.0 1.0	11.3 13.4	
				01 M		9 10, 11	1.0 1.0	9.0 11.0	
				02 M		9 10, 11	1.0 1.0	11.3 13.4	
			M	01		9	1.0	9.0	
			D	B, S, Q, V			1.0	9.0	
			P, L, R				1.0	9.0	

See footnotes at end of table.

TABLE I. Electrical performance characteristics - Continued.

Test and MIL-STD-883 test method 1/	Symbol	Test Conditions 2/ $-55°C \le T_C \le +125°C$ $+4.5\ V \le V_{CC} \le +5.5\ V$ unless otherwise specified		Device type 3/ and device class	V_{CC}	Group A subgroups	Limits 2/		Unit
							Min	Max	
Propagation delay time, output disable, OEn to mYn 3003	t_{PHZ}, t_{PLZ} 5/ 6/ 15/ 16/	C_L = 50 pF minimum, R_L = 500Ω, See figure 5		01	4.5 V	9, 11	1.0	9.5	ns
				B, S, Q, V		10	1.0	11.5	
				02		9, 11	1.0	10.6	
				B, S, Q, V		10	1.0	11.6	
				01		9	1.0	9.5	
				M		10, 11	1.0	11.5	
				02		9	1.0	10.6	
				M		10, 11	1.0	11.6	
			M	01		9	1.0	9.5	
			D	B, S, Q, V			1.0	9.5	
			P, L, R				1.0	9.5	

1/ For tests not listed in the referenced MIL-STD-883 (e.g. ΔI_{CC}), utilize the general test procedure under the conditions listed herein. All inputs and outputs shall be tested, as applicable, to the tests in table I herein.

2/ Each input/output, as applicable shall be tested at the specified temperature for the specified limits. Output terminals not designated shall be high level logic, low level logic, or open, except as follows:

a. V_{IC} (pos) tests, the GND terminal can be open. T_C = +25°C.

b. V_{IC} (neg) tests, the V_{CC} terminal shall be open. T_C = +25°C.

c. All I_{CC} and ΔI_{CC} tests, the output terminal shall be open. When performing these tests, the current meter shall be placed in the circuit such that all current flows through the meter.

For negative and positive voltage and current values: The sign designates the potential difference in reference to GND and the direction of current flow respectively; and the absolute value of the magnitude, not the sign, is relative to the minimum and maximum limits, as applicable, listed herein.

3/ The word "All" in the device type and device class column, means non-RHA limits for all device types and classes. Where M, D, P, L, and R in the conditions column are postirradiation limits for those device types and classes specified in the device type and device class column.

4/ This test is guaranteed, if not tested, to the limits specified in table I.

5/ RHA samples do not have to be tested at -55°C and +125°C prior to irradiation.

6/ When performing post irradiation electrical measurements for RHA level, T_A = +25°C. Limits shown are guaranteed at T_A = +25°C ±5°C.

7/ Transmission driving tests are performed at V_{CC} = 5.5 V dc with a 2 ms duration maximum. This test may be performed using $V_{IN} = V_{CC}$ or GND. When $V_{IN} = V_{CC}$ or GND is used, the test is guaranteed for V_{IN} = 2.0 V or 0.8 V.

8/ Three-state output conditions are required.

9/ Power dissipation capacitance (C_{PD}) determines the no load dynamic power consumption,
$P_D = (C_{PD} + C_L) (V_{CC} \times V_{CC})f + (I_{CC} \times V_{CC}) + (n \times d \times \Delta I_{CC} \times V_{CC})$.
The dynamic current consumption,
$I_S = (C_{PD} + C_L)V_{CC}f + I_{CC} + n \times d \times \Delta I_{CC}$.
For both P_D and I_S: n is the number of device inputs at TTL levels, f is the frequency of the input signal, and d is the duty cycle of the input signal.

10/ This test may be performed either one input at a time (preferred method) or with all input pins simultaneously at $V_{IN} = V_{CC} - 2.1$ V (alternate method). Classes B, S, Q, and V shall use the preferred method. When the test is performed using the alternate test method: the maximum limits are equal to the number of inputs at a high TTL input level times 1.6 mA; and the preferred method and limits are guaranteed.

11/ This test is for qualification only. Ground bounce tests are performed on a nonswitching (quiescent) output and are used to measure the magnitude of induced noise caused by other simultaneously switching outputs. The test is performed on a low noise bench test fixture with all outputs fully dc loaded (I_{OL} maximum and I_{OH} minimum = i.e., ±24 mA) and 50pF of load capacitance (see figure 4). The loads must be located as close as possible to the device output. Inputs are then conditioned with 1 MHz pulse ($t_r = t_f = 3.5 \pm 1.5$ ns) switching simultaneously and in phase such that one output is forced low and all others (possible) are switched. The low level ground bounce noise is measured at the quiet output using a F.E.T. oscilloscope probe with at least 1 MΩ impedance. Measurement is taken from the peak of the largest positive pulse with respect to the nominal low level output voltage (figure 4). The device inputs are then conditioned such that the output under test is at a high nominal V_{OH} level. The high level ground bounce measurement is then measured from nominal V_{OH} level to the largest negative peak. This procedure is repeated such that all outputs are tested at a high and low level with a maximum number of outputs switching.

12/ When used in synchronous TTL compatible systems, ground bounce (V_{GBL} and V_{GBH}) = 2,000 mV can be a possible problem.

13/ See JEDEC STD. 17 for electrically induced latch-up test methods and procedures. The values listed for $V_{trigger}$, $I_{trigger}$ and V_{over}, are to be accurate within ±5 percent.

14/ Tests shall be performed in sequence, attributes data only. Functional tests shall include the truth table and other logic patterns used for fault detection. Functional tests shall be performed in sequence as approved by the qualifying activity on qualified devices. $H \geq 2.5$ V, $L \leq 2.5$ V; high inputs = 2.4 V and low inputs = 0.4 V. The input voltage levels have the allowable tolerances per MIL-STD-883 already incorporated. Functional tests at $V_{CC} = 4.5$ V are worst case for RHA specified devices.

15/ Device classes B and S are tested at $V_{CC} = 4.5$ V at $T_C = +125°C$ for sample testing and at $V_{CC} = 4.5$ V at $T_C = +25°C$ for screening. Other voltages of V_{CC} and temperatures are guaranteed, if not tested, see 4.4.1d.

16/ AC limits at $V_{CC} = 5.5$ V are equal to the limits at $V_{CC} = 4.5$ V and guaranteed by testing at $V_{CC} = 4.5$ V. Minimum ac limits for $V_{CC} = 5.5$ V are 1.0 ns and guaranteed by guardbanding the $V_{CC} = 4.5$ V minimum limits to 1.5 ns. For propagation delay tests, all paths must be tested.

Device types	01		02	
Case outlines	R and S	2	L	3
Terminal number	Terminal symbol			
1	$\overline{OE1}$	$\overline{OE1}$	1Y1	NC
2	1A1	1A1	2Y1	V_{CC}
3	4Y2	4Y2	3Y1	4A1
4	2A1	2A1	4Y1	3A1
5	3Y2	3Y2	GND	2A1
6	3A1	3A1	GND	1A1
7	2Y2	2Y2	GND	OE1
8	4A1	4A1	GND	NC
9	1Y2	1Y2	1Y2	1Y1
10	GND	GND	2Y2	2Y1
11	1A2	1A2	3Y3	3Y1
12	4Y1	4Y1	4Y2	4Y1
13	2A2	2A2	OE2	GND
14	3Y1	3Y1	4A2	GND
15	3A2	3A2	3A2	NC
16	2Y1	2Y1	2A2	GND
17	4A2	4A2	1A2	GND
18	1Y1	1Y1	V_{CC}	1Y2
19	OE2	OE2	V_{CC}	2Y2
20	V_{CC}	V_{CC}	4A1	3Y2
21	---	---	3A1	4Y2
22	---	---	2A1	NC
23	---	---	1A1	OE2
24	---	---	OE1	4A2
25	---	---	---	3A2
26	---	---	---	2A2
27	---	---	---	1A2
28	---	---	---	V_{CC}

FIGURE 1. Terminal connections.

Device types 01 and 02		
Inputs		Outputs
$\overline{OEn}$	mAn	mYn
L	L	L
L	H	H
H	X	Z

H = High voltage level
L = Low voltage level
X = Irrelevant
Z = High impedance

FIGURE 2. Truth table.

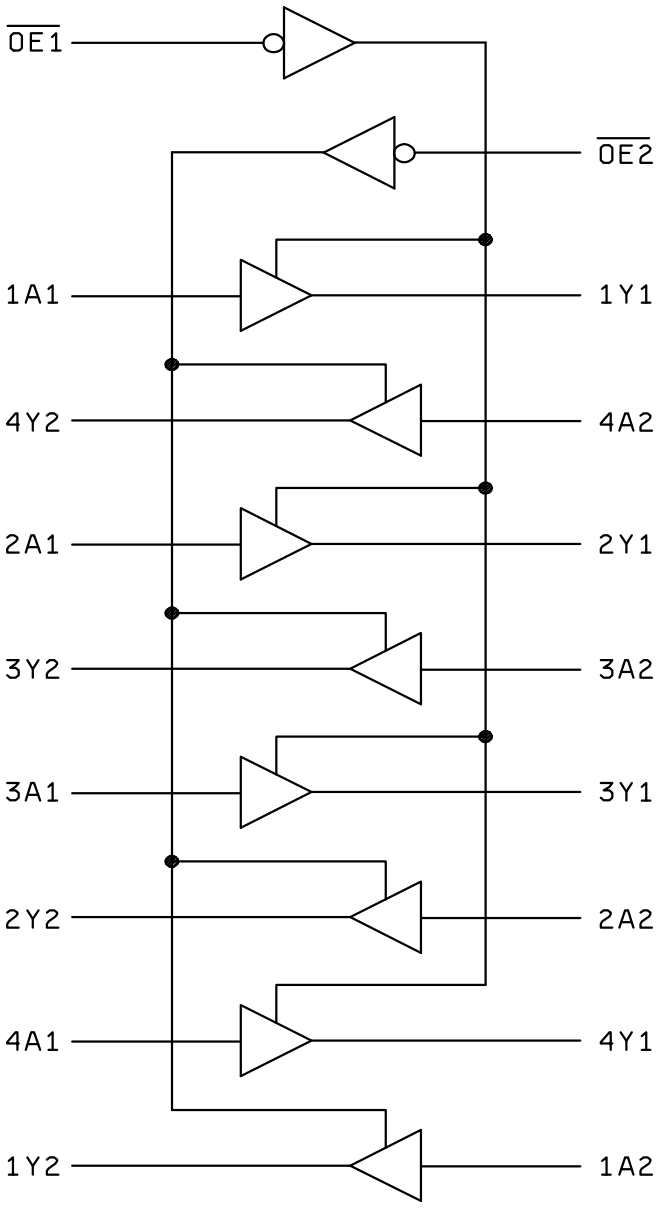
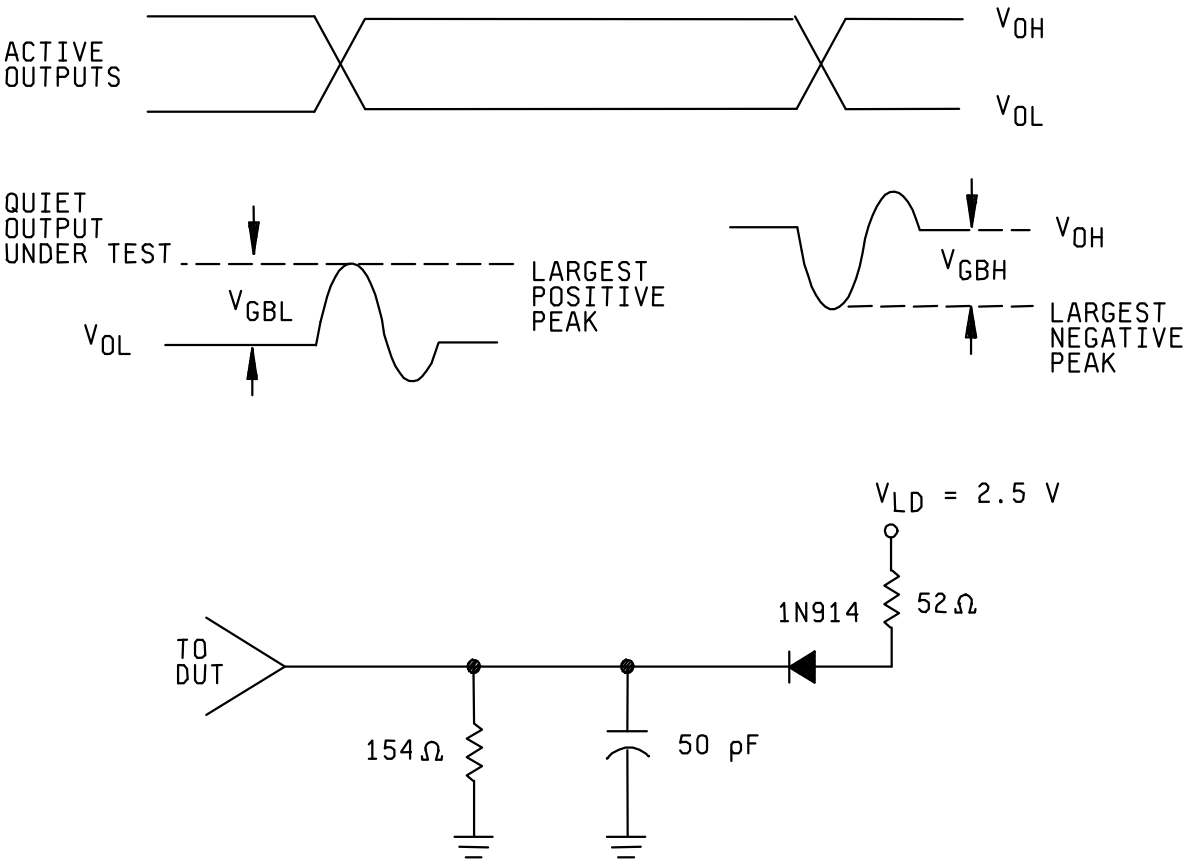
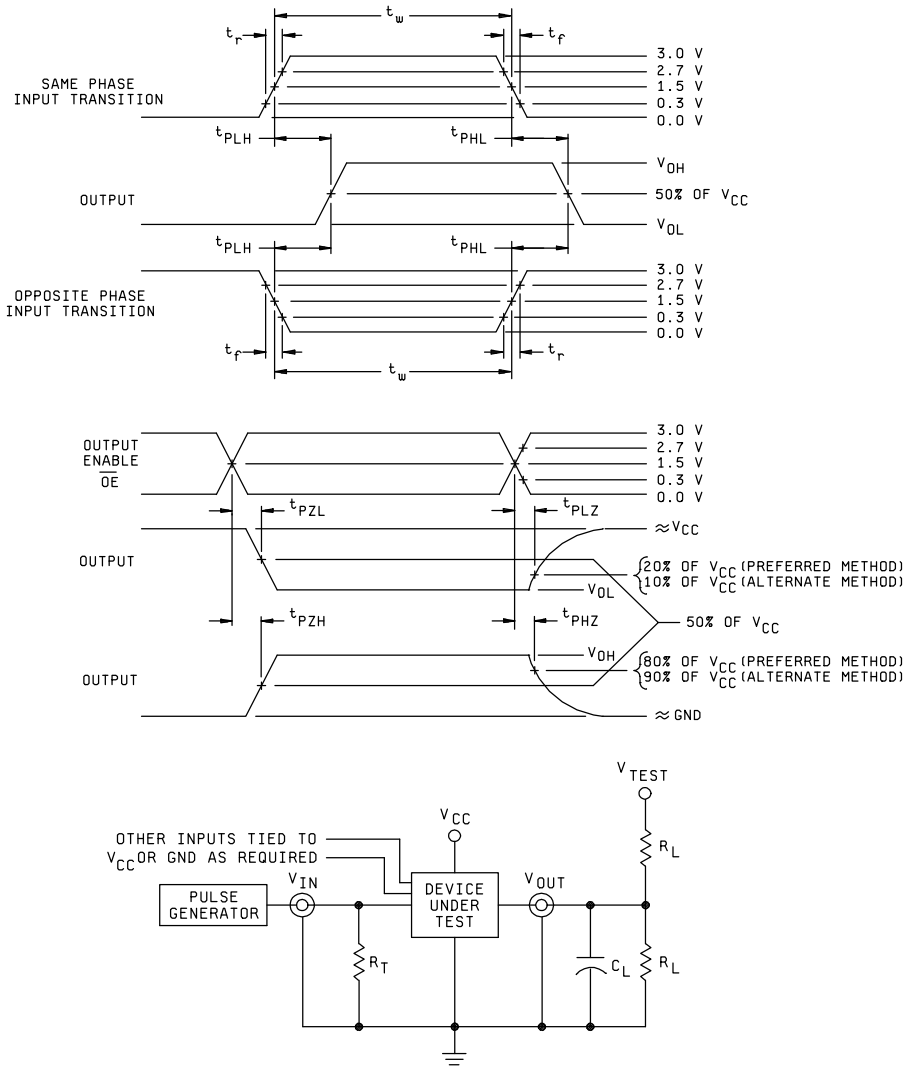


FIGURE 3. Logic diagram.



Note: Resistor and capacitor tolerances = ±10%

FIGURE 4. Ground bounce waveforms and test circuit.



Notes:

1. Preferred method - used for device type 02:
   When measuring t_{PHZ} and t_{PZH}: V test = GND
   When measuring t_{PLZ} and t_{PZL}: V test = 2 X V_{CC}
   When measuring t_{PLH} and t_{PHL}: V test = open
   Alternate method - used for device type o1:
   When measuring t_{PLZ} and t_{PZL}: V test = 2 X V_{CC}
   When measuring t_{PHZ},t_{PZH},$t_{PLH}$and t_{PHL}: V test = open
2. C_L = 50 pF minimum or equivalent (includes test jig and probe capacitance).
3. R_T = 50Ω or equivalent. R_L = 500Ω or equivalent.
4. Input signal from pulse generator: V_{IN} = 0.0 V to 3.0 V; PRR ≤ 10 Mhz; t_r ≤ 3 ns; t_f ≤ 3 ns; duty cycle = 50 percent.
5. Timing parameters shall be tested at a minimum input frequency of 1 MHz.
6. Outputs are measured one at a time with one output per measurement.

FIGURE 5. Switching waveforms and test circuit.

4. QUALITY ASSURANCE PROVISIONS

4.1 Sampling and inspection. For device classes Q and V, sampling and inspection procedures shall be in accordance with MIL-PRF-38535 or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. For device class M, sampling and inspection procedures shall be in accordance with MIL-PRF-38535, appendix A. For device class B, sampling and inspection procedures shall be in accordance with MIL-PRF-38535, Appendix A and method 5005 of MIL-STD-883, except as modified herein. For device class S, sampling and inspection procedures shall be in accordance with MIL-PRF-38535, Appendix A and methods 5005 and 5007 of MIL-STD-883, except as modified herein

4.1.1 Burn-in and life test circuits. For device classes B and S, the burn-in and life test circuits shall be constructed so that the devices are stressed at the maximum operating conditions stated in 4.2.1a5 or 4.2.1a6 as applicable, or equivalent as approved by the qualifying activity.

4.2 Screening. For device classes Q and V, screening shall be in accordance with MIL-PRF-38535, and shall be conducted on all devices prior to qualification and technology conformance inspection. For device class M, screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection. For device classes B and S, screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to qualification and quality conformance inspection.

4.2.1 Additional criteria for device classes M, B and S.

a. Burn-in test, method 1015 of MIL-STD-883.

(1) Test condition A, B, C or D. For device class M, the test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015. For device classes B and S, the test circuit shall be submitted to the qualifying activity.

(2) T_A = +125°C, minimum.

(3) Delete the sequence specified in 3.1.10 through 3.1.14 of method 5004 and substitute lines 1 through 7 requirements of table IIA herein.

(4) For device class M, unless otherwise noted, the requirements for device class B in method 1015 of MIL-STD-883 shall be followed.

(5) Static burn-in, test condition A, test method 1015 of MIL-STD-883. Test duration for each static test shall be 24 hours minimum for class S devices and in accordance with table I of method 1015 for class B devices.

(a) For static burn-in I, all inputs shall be connected to GND. Outputs may be open or connected to $V_{CC}/2$ ±0.5 V. Resistors R1 are optional on both inputs and open outputs, and required on outputs connected to $V_{CC}/2$ ±0.5 V.
R1 = 220Ω to 47 kΩ.

(b) For static burn-in II, all inputs shall be connected through the R1 resistors to V_{CC}. Outputs may be open or connected to $V_{CC}/2$ ±0.5 V. Resistors R1 are optional on open outputs, and required on outputs connected to $V_{CC}/2$ ±0.5 V. R1 = 220Ω to 47 kΩ.

(c) V_{CC} = 5.5 V ±0.5 V.

(6) Dynamic burn-in, test condition D, method 1015 of MIL-STD-883,

(a) Input resistors = 220Ω to 2 kΩ ±20 percent.

(b) Output resistors = 220Ω ±20 percent.

(c) V_{CC} = 5.5 V ±0.5 V.

(d) The output enable control pin(s) shall be connected through the resistors in parallel to V_{CC} or GND, as applicable, to enable the outputs. All other inputs shall be connected through the resistors in parallel to a common clock pulse (CP) as applicable. Outputs shall be connected through the resistors to $V_{CC}/2 \pm 0.5$ V.

(e) CP = 25 kHz to 1 MHz square wave; duty cycle = 50 percent ±15 percent; V_{IH} = 4.5 V to V_{CC}, V_{IL} = 0 V ±0.5 V; t_r, $t_f \leq 100$ ns.

b. Interim and final electrical test parameters shall be as specified in table IIA herein.

c. For class S devices, post dynamic burn-in, or class B devices, post static burn-in, electrical parameter measurements may, at the manufacturer's option, be performed separately or included in the final electrical parameter requirements.

TABLE IIA. Electrical test requirements.

Test requirements	Subgroups (in accordance with MIL-STD-883, method 5005, table I)			Subgroups (in accordance with MIL-PRF-38535, table III)	
	Device class M	Device 1/ class B	Device 2/ class S	Device class Q	Device class V
Interim electrical parameters, method 5004		1	1	1	1
Static burn-in I, method 1015 (4.2.1a)	3/	Not required	Required 4/	Not required	Required 4/
Interim electrical parameters, method 5004 (4.2.1b)			1 5/		1 5/
Static burn-in II, method 1015 (4.2.1a)	3/	Required 6/	Required 4/	Required 6/	Required 4/
Interim electrical parameters, method 5004 (see 4.2.1b)		1 1/, 5/	1 2/, 5/	1 1/, 5/	1 2/, 5/
Dynamic burn-in I, method 1015 (4.2.1a)	3/	Not required	Required 4/	Not required	Required 4
Interim electrical parameters, method 5004 (4.2.1b)			1 5/		1 5/
Final electrical parameters, method 5004	1, 2, 3, 7, 8, 9 1/	1, 2, 7, 9 1/, 6/	1, 2, 7, 9 2/	1, 2, 3, 7, 8, 9, 10, 11 1/, 6/	1, 2, 3, 7,8, 9, 10, 11 2/, 5/
Group A test requirements, method 5005 (4.4.1)	1, 2, 3, 4, 7, 8, 9, 10, 11	1, 2, 3, 4, 7, 8, 9, 10, 11	1, 2, 3, 4, 7, 8, 9, 10, 11	1, 2, 3, 4, 7, 8, 9, 10, 11	1, 2, 3, 4, 7, 8, 9, 10, 11
Group B end-point electrical parameters, method 5005 (4.4.2)			1, 2, 3, 7, 8, 9, 10, 11 5/		
Group C end-point electrical parameters, method 5005 (4.4.3)	1, 2, 3	1, 2 5/		1, 2, 3 5/	1, 2, 3, 7, 8, 9, 10, 11 5/
Group D end-point electrical parameters, method 5005 (4.4.4)	1, 2, 3	1, 2	1, 2, 3	1, 2, 3	1, 2, 3
Group E end-point electrical parameters, method 5005 (4.4.5)	1, 7, 9	1, 7, 9	1, 7, 9	1, 7, 9	1, 7, 9

See footnotes on next page.

1/ PDA applies to subgroup 1.

2/ PDA applies to subgroups 1 and 7.

3/ The required test condition used for burn-in shall be that submitted to DSCC-VQC with the certificate of compliance. See 4.2.1a herein.

4/ On all class S lots, the device manufacturer shall maintain read-and-record data (as a minimum on disk) for burn-in electrical parameters (group A, subgroup 1), in accordance with test method 5004 of MIL-STD-883. For pre-burn-in and interim electrical parameters the read-and-record requirements are for delta measurements only.

5/ Delta limits as specified in table III shall be required where specified, and the delta limits shall be completed with reference to the zero hour electrical parameters.

6/ The device manufacturer may at his option either complete subgroup 1 electrical parameter measurements, including delta measurements, within 96 hours after burn-in completion (removal of bias); or may complete subgroup 1 electrical measurements without delta measurements within 24 hours after burn-in completion (removal of bias). When the manufacturer elects to perform the subgroup 1 electrical parameter measurements without delta measurements, there is no requirement to perform the pre-burn-in electrical tests (first interim electrical parameters test in table IIA).

4.2.2 Additional criteria for device classes Q and V.

a. The burn-in test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document revision level control of the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015 of MIL-STD-883.

b. Interim and final electrical test parameters shall be as specified in table IIA herein.

c. Additional screening for device class V beyond the requirements of device class Q shall be as specified in MIL-PRF-38535, appendix B and as detailed in table IIB herein.

4.2.3 Percent defective allowable (PDA).

a. The PDA for class S devices shall be 5 percent for static burn-in and 5 percent for dynamic burn-in, based on the exact number of devices submitted to each separate burn-in.

b. Static burn-in I and II failures shall be cumulative for determining the PDA.

c. The PDA for class B devices shall be in accordance with MIL-PRF-38535, appendix A for static burn-in. Dynamic burn-in is not required.

d. The PDA for class M devices shall be in accordance with MIL-PRF-38535, appendix A for static burn-in and dynamic burn-in.

e. Those devices whose measured characteristics, after burn-in, exceed the specified delta limits or electrical parameter limits specified in table I, subgroup I, are defective and shall be removed from the lot. The verified number of failed devices times 100 divided by the total number of devices in the lot initially submitted to burn-in shall be used to determine the percent defective for the lot and the lot shall be accepted or rejected based on the specified PDA.

4.3 Qualification inspection.

4.3.1 Qualification inspection for device classes B and S. Qualification inspection for device classes B and S, shall be in accordance with MIL-PRF-38535, appendix A. Inspections to be performed shall be those specified in method 5005 of MIL-STD-883 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.5).

4.3.2 Qualification inspection for device classes Q and V. Qualification inspection for device classes Q and V shall be in accordance with MIL-PRF-38535. Inspections to be performed shall be those specified in MIL-PRF-38535 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.5).

4.3.3 Electrostatic discharge sensitivity qualification inspection. Electrostatic discharge sensitivity (ESDS) testing shall be in accordance with MIL-STD-883, method 3015. ESDS testing shall be measured only for initial qualification and after process or design changes which may affect ESDS classification. For device classes Q and V, only those device types that pass ESDS testing at 2000 volts or greater shall be considered as conforming to the requirements of this specification.

Table IIB. Additional screening for device class V.

Test	MIL-STD-883, test method	Lot requirement
Particle impact noise detection	2020	100%
Internal visual	2010, condition A or approved alternate	100%
Nondestructive bond pull	2023 or approved alternate	100%
Reverse bias burn-in	2010	100%
Burn-in	1015, total of 240 hours at +125°C	100%
Radiographic	2012	100%

Table III. Burn-in and operating life test Delta parameters (+25°C).

Parameter 1/	Device types	Limits
I_{CCH}, I_{CCL}, I_{CCZ}	All	±100 nA

1/ These parameters shall be recorded before and after the required burn-in and life tests to determine delta limits.

4.4 Conformance inspection. Technology conformance inspection for classes Q and V shall be in accordance with MIL-PRF-38535 including groups A, B, C, D, and E inspections and as specified herein. Quality conformance inspection for device class M shall be in accordance with MIL-PRF-38535, appendix A and as specified herein. Quality conformance inspection for device classes B and S shall be in accordance with MIL-PRF-38535, appendix A and as specified herein. Inspections to be performed for device classes M, B, and S shall be those specified in method 5005 of MIL-STD-883 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.5).

4.4.1 Group A inspection.

a. Tests shall be as specified in table IIA herein.

b. C_{IN}, C_{OUT}, and C_{PD} shall be measured only for initial qualification and after process or design changes which may affect capacitance. C_{IN} and C_{OUT} shall be measured between the designated terminal and GND at a frequency of 1 MHz. C_{PD} shall be tested in accordance with the latest revision of JEDEC Standard No. 20 and table I herein. For C_{IN}, C_{OUT}, and C_{PD}, test all applicable pins on five devices with zero failures.

c. For device class M, subgroups 7 and 8 tests shall be sufficient to verify the truth table in figure 2 herein. The test vectors used to verify the truth table shall test all possible input to output logic patterns. For device classes B and S, subgroups 7 and 8 tests shall be sufficient to verify the truth table as approved by the qualifying activity. For device classes Q and V, subgroups 7 and 8 shall include verifying the functionality of the device.

d. Latch-up and ground bounce tests are required for device classes B, S, Q, and V. These tests shall be performed only for initial qualification and after process or design changes which may affect the performance of the device. Latch-up tests shall be considered destructive. For latch-up and ground bounce tests, test all applicable pins on five devices with zero failures.

f. For device classes B and S, subgroups 9 and 11 tests shall be measured only for initial qualification and after process or design changes which may affect dynamic performance.

4.4.2 Group B inspection. The group B inspection end-point electrical parameters shall be as specified in table IIA herein and as follows.

a. Class S steady-state life (accelerated) shall be conducted using test condition D of method 1005 of MIL-STD-883 and the circuit described in 4.2.1a6 herein, or equivalent as approved by the qualifying activity. The actual test circuit used shall be submitted to the qualifying activity.

b. End-point electrical parameters shall be as specified in table IIA herein. Delta limits shall apply only to subgroup 5 of group B inspections and shall consist of tests specified in table III herein.

4.4.3 Group C inspection. The group C inspection end-point electrical parameters shall be as specified in table IIA herein.

4.4.3.1 Additional criteria for device classes M and B. Steady-state life test conditions, method 1005 of MIL-STD-883:

a. End-point electrical parameters shall be as specified in table IIA herein. Delta limits shall apply only to subgroup 1 of group C inspection and shall consist of tests specified in table III herein.

b. Test condition A, B, C or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005 of
MIL-STD-883.

c. T_A = +125°C, minimum.

d. Test duration: 1,000 hours, except as permitted by method 1005 of MIL-STD-883.

4.4.3.2 Additional criteria for device classes Q and V. The steady-state life test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The test circuit shall be maintained under document revision level control by the device manufacturer's TRB in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005 of MIL-STD-883.

4.4.4 Group D inspection. The group D inspection end-point electrical parameters shall be as specified in table IIA herein.

4.4.5 Group E inspection. Group E inspection is required only for parts intended to be marked as radiation hardness assured (see 3.5 herein). RHA levels for device classes B, S, Q, and V shall be M, D, and R and for device class M shall be M and D. RHA quality conformance inspection sample tests shall be performed at the RHA level specified in the acquisition document.

a. RHA tests for device classes B and S for levels M, D, and R or for device class M for levels M and D shall be performed through each level to determine at what levels the devices meet the RHA requirements. These RHA tests shall be performed for initial qualification and after design or process changes which may affect the RHA performance of the device.

b. End-point electrical parameters shall be as specified in table IIA herein.

c. Prior to total dose irradiation, each selected sample shall be assembled in its qualified package. It shall pass the specified group A electrical parameters in table I for subgroups specified in table IIA herein.

d. For device classes Q and V, the devices or test vehicle shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535 for the RHA level being tested. For device classes M, B, and S, the devices shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535, appendix A for the RHA level being tested. All device classes must meet the postirradiation end-point electrical parameter limits as defined in table I at T_A = +25°C ±5°C, after exposure, to the subgroups specified in table IIA herein.

e. Prior to and during total dose irradiation characterization and testing, the devices for characterization shall be biased so that 50 percent are at inputs high and 50 percent are at inputs low, and the devices for testing shall be biased to the worst case condition established during characterization. The devices shall be biased as follows:

(1) Inputs tested high, V_{CC} = 5.5 V dc +5 percent, R_{CC} = 10Ω ±20 percent, V_{IN} = 5.0 V dc +5 percent, R_{IN} = 1 kΩ ±20 percent and all outputs are open. The output enable control pin(s) shall be connected to R_{IN} in parallel to V_{CC} or GND, as applicable, to enable the outputs.

(2) Inputs tested low, V_{CC} = 5.5 V dc +5 percent, R_{CC} = 10Ω ±20 percent, V_{IN} = 0.0 V dc, R_{IN} = 1 kΩ ±20 percent and all outputs are open. The output enable control pin(s) shall be connected to R_{IN} in parallel to V_{CC} or GND, as applicable, to enable the outputs.

f. For device classes M, B, and S, subgroups 1 and 2 in table V, method 5005 of MIL-STD-883 shall be tested as appropriate for device construction. Device classes Q and V, shall be tested as appropriate for device construction, as determined in the device manufacturers QM plan.

g. When specified in the purchase order or contract, a copy of the RHA delta limits shall be supplied.

4.5 Methods of inspection. Methods of inspection shall be specified as follows:

4.5.1 Voltage and current. Unless otherwise specified, all voltages given are referenced to the microcircuit GND terminal. Currents given are conventional current and positive when flowing into the referenced terminal.

5. PACKAGING

5.1 Packaging requirements. The requirements for packaging shall be in accordance with MIL-PRF-38535 for device classes Q and V or MIL-PRF-38535, appendix A for device classes M, B, and S.

6. NOTES

6.1 Intended use. Microcircuits conforming to this drawing are intended for use for Government microcircuit applications (original equipment), design applications, and logistics purposes.

6.1.1 Replaceability. Microcircuits covered by this drawing will replace the same generic device covered by a contractor prepared specification or drawing.

6.1.2 Substitutability. Device class Q devices will replace device class M devices.

6.2 Configuration control of SMD's. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished using DD Form 1692, Engineering Change Proposal.

6.3 Record of users. Military and industrial users should inform Defense Supply Center Columbus when a system application requires configuration control and which SMD's are applicable to that system. DSCC will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronic devices (FSC 5962) should contact DSCC-VA, telephone (614) 692-0544.

6.4 Comments. Comments on this drawing should be directed to DSCC-VA, Columbus, Ohio 43216-5000, or telephone (614) 692-0547.

6.5 Abbreviations, symbols, and definitions. The abbreviations, symbols, and definitions used herein are defined in MIL-PRF-38535 and MIL-HDBK-1331.

6.6 Sources of supply.

6.6.1 Sources of supply for device classes B and S. Sources of supply for device classes B and S are listed in QML-38535. The vendors listed in QML-38535 have submitted a certificate of compliance (see 3.6 herein) to DSCC-VA and have agreed to this drawing.

6.6.2 Sources of supply for device classes Q and V. Sources of supply for device classes Q and V are listed in QML-38535. The vendors listed in QML-38535 have submitted a certificate of compliance (see 3.6 herein) to DSCC-VA and have agreed to this drawing.

6.6.3 Approved sources of supply for device class M. Approved sources of supply for class M are listed in MIL-HDBK-103. The vendors listed in MIL-HDBK-103 have agreed to this drawing and a certificate of compliance (see 3.6 herein) has been submitted to and accepted by DSCC-VA.

A.1 SCOPE

A.1.1 Scope. This appendix contains the PIN substitution information to support the one part-one part number system. For new designs, after the date of this document the NEW PIN shall be used in lieu of the OLD PIN. For existing designs prior to the date of this document the NEW PIN can be used in lieu of the OLD PIN. This appendix is a mandatory part of the specification. The information contained herein is intended for compliance. The PIN substitution data shall be as follows.

A.2 APPLICATION DOCUMENTS This section is not applicable to this appendix.

A.3 SUBSTITUTION DATA

New PIN	Old PIN
5962-8776001MRX	5962-8776001RX
5962-8776001MSX	5962-8776001SX
5962-8776001M2X	5962-87760012X
5962-8776001MLX	5962-8776001LX
5962-8776001M3X	5962-87760013X

STANDARD MICROCIRCUIT DRAWING BULLETIN

DATE: 01-06-29

Approved sources of supply for SMD 5962-87760 are listed below for immediate acquisition information only and shall be added to MIL-HDBK-103 and QML-38535 during the next revision. MIL-HDBK-103 and QML-38535 will be revised to include the addition or deletion of sources. The vendors listed below have agreed to this drawing and a certificate of compliance has been submitted to and accepted by DSCC-VA. This bulletin is superseded by the next dated revision of MIL-HDBK-103 and QML-38535.

Standard microcircuit drawing PIN 1/	Vendor CAGE number	Vendor similar PIN 2/
5962-8776001MRA	27014 01295	54ACT244DMQB SNJ54ACT244J
5962-8776001MSA	27014 01295	54ACT244FMQB SNJ54ACT244W
5962-8776001M2A	27014 01295	54ACT244LMQB SNJ54ACT244FK
5962-8776001BRA	27014	JM54ACT244BRA
5962-8776001BSA	27014	JM54ACT244BSA
5962-8776001B2A	27014	JM54ACT244B2A
5962-8776001SRA	3/	54ACT244
5962-8776001SSA	3/	54ACT244
5962-8776001S2A	27014	JM54ACT244S2A
5962-87760023A	3/	54ACT11244
5962-8776002LA	3/	54ACT11244
5962-8776002M3A	3/	54ACT11244
5962-8776002MLA	3/	54ACT11244
5962R8776001BRA	27014	JM54ACT244BRA-RH
5962R8776001BSA	27014	JM54ACT244BSA-RH
5962R8776001B2A	27014	JM54ACT244B2A-RH
5962R8776001SRA	27014	JM54ACT244SRA-RH
5962R8776001SSA	27014	JM54ACT244SSA-RH
5962R8776001S2A	27014	JM54ACT244S2A-RH

1/ The lead finish shown for each PIN representing a hermetic package is the most readily available from the manufacturer listed for that part. If the desired lead finish is not listed contact the vendor to determine its availability.

2/ Caution. Do not use this number for item acquisition. Items acquired to this number may not satisfy the performance requirements of this drawing.

3/ Not available from an approved source of supply.

Vendor CAGE number	Vendor name and address
27014	National Semiconductor 2900 Semiconductor Drive P.O. Box 58090 Santa Clara, CA 95052-8090 Point of contact: 5 Foden Road South Portland, ME 04106
01295	Texas Instruments 8505 Forest Ln. P.O. Box 660199 Dallas, TX 75243 Point of contact: U.S. Highway 75 South P.O. Box 84 M/S 853 Sherman, TX 75090-9493